

IN THE CLAIMS

1. (canceled)

~~17~~ 2. (previously presented): The semiconductor apparatus according to claim 32, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

~~18~~ 3. (currently amended): The semiconductor apparatus according to claim ~~2~~¹⁷, comprising:

[[a]] wherein the second-conductivity-type \pm area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor, and

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

4. (canceled)

~~19~~ 5. (previously presented): The semiconductor apparatus according to claim ~~32~~¹⁶, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

~~20~~ 6. (previously presented): The semiconductor apparatus according to claim ~~32~~¹⁶, wherein said first-conductivity-type MOS protection transistor is higher in electrostatic destruction withstanding voltage than said first-conductivity-type MOS output transistor.

~~21~~ 7. (original): The semiconductor apparatus according to claim ~~6~~²⁰, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

22/
8. (currently amended): The semiconductor apparatus according to claim 7, comprising:

[[a]] wherein the second-conductivity-type \pm area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

23/
9. (previously presented): The semiconductor apparatus according to claim 8, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

24/
10. (previously presented): The semiconductor apparatus according to claim 9, wherein the drain electrode of said first-conductivity-type MOS protection transistor is formed closer to the output electrode than the drain electrode of said first-conductivity-type MOS output transistor.

25/
11. (original): The semiconductor apparatus according to claim 10, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

26/
12. (currently amended): The semiconductor apparatus according to claim 11, comprising:

25/
[[a]] wherein the second-conductivity-type \pm area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~27~~ 13. (previously presented): The semiconductor apparatus according to claim ~~10~~²⁴, wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected by an electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~28~~ 14. (original): The semiconductor apparatus according to claim ~~13~~²⁷, wherein said first-conductivity-type MOS output transistor and said first-conductivity-type MOS protection transistor are of an SOI structure.

~~29~~ 15. (currently amended): The semiconductor apparatus according to claim ~~14~~²⁸, comprising:
[[a]] wherein the second-conductivity-type \pm area is connected to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor,

wherein the gate electrode of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

~~1~~ 16. (currently amended): A semiconductor apparatus which protects a first-conductivity-type MOS output transistor and a second-conductivity-type MOS output transistor against a surge entering through an output electrode connected to each of drains of said first-conductivity-type MOS output transistor whose source is connected to ground and said second-conductivity-type MOS output transistor whose source is connected to a power supply, said apparatus comprising:

a first-conductivity-type MOS protection transistor having a drain connected to the drain of said first-conductivity-type MOS output transistor, a source connected to a source of said first-conductivity-type MOS output transistor, and a gate connected to a second-conductivity-type layer under a gate of said first-conductivity-type MOS output transistor; and

a second-conductivity-type MOS protection transistor having a drain connected to the drain of said second-conductivity-type MOS output transistor, a source connected to a source of said second-conductivity-type MOS output transistor, and a gate connected to a first-conductivity-type layer under a gate of said second-conductivity-type MOS output transistor;

wherein said first-conductivity-type MOS output transistor further includes a second-conductivity-type + area which is formed in said second-conductivity-type layer and substantially surrounds said drain electrode and said source electrode.

² ~~17~~. (original): The semiconductor apparatus according to claim ~~16~~¹, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

³ ~~18~~. (currently amended): The semiconductor apparatus according to claim ~~17~~², comprising:
[[a]] wherein the second-conductivity-type + area is connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and comprising

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type + area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~4~~ 19. (original): The semiconductor apparatus according to claim ~~16~~, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~5~~ 20. (original): The semiconductor apparatus according to claim ~~16~~, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~6~~ 21. (original): The semiconductor apparatus according to claim ~~16~~, wherein said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are higher in electrostatic destruction withstand voltage than said first-conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~7~~ 22. (original): The semiconductor apparatus according to claim ~~21~~, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection

transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~8~~ 23. (currently amended): The semiconductor apparatus according to claim ~~22~~⁷, comprising:

a second-conductivity-type \pm area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~9~~ 24. (original): The semiconductor apparatus according to claim ~~21~~⁶, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~10~~ 25. (original): The semiconductor apparatus according to claim ~~21~~⁶, wherein the drains of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are formed closer to the output electrode than the drains of said first-

conductivity-type MOS output transistor and said second-conductivity-type MOS output transistor.

~~11~~ 26. (original): The semiconductor apparatus according to claim ~~10~~ 25, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~12~~ 27. (currently amended): The semiconductor apparatus according to claim ~~11~~ 26, comprising:
a second-conductivity-type \pm area connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor; and
a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,
wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and
wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~13~~ 28. (original): The semiconductor apparatus according to claim ~~10~~ 25, wherein the gates of said first-conductivity-type MOS protection transistor and said second-conductivity-type MOS protection transistor are connected by electrode wirings respectively to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor and to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~14~~
29. (original): The semiconductor apparatus according to claim ~~28~~¹³, wherein said first-conductivity-type MOS output transistor, said first-conductivity-type MOS protection transistor, said second-conductivity-type MOS output transistor, and said second-conductivity-type MOS protection transistor are of an SOI structure.

~~15~~
30. (currently amended): The semiconductor apparatus according to claim ~~29~~¹⁴, comprising:

[[a]] wherein the second-conductivity-type \pm area is connected to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor;
and

a first-conductivity-type area connected to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor,

wherein the gate of said first-conductivity-type MOS protection transistor is connected via said second-conductivity-type \pm area to said second-conductivity-type layer under the gate of said first-conductivity-type MOS output transistor, and

wherein the gate of said second-conductivity-type MOS protection transistor is connected via said first-conductivity-type area to said first-conductivity-type layer under the gate of said second-conductivity-type MOS output transistor.

~~30~~
31. (previously presented): The semiconductor apparatus according to claim ~~32~~¹⁶, wherein the gate electrode of said first-conductivity-type MOS protection transistor is directly connected by the electrode wiring to said second-conductivity-type layer under the gate electrode of said first-conductivity-type MOS output transistor.

16
~~22.~~ (currently amended): A semiconductor apparatus comprising:

an output electrode from which an output signal of the semiconductor apparatus is output;

a first-conductivity-type MOS output transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to a ground voltage terminal, a gate electrode connected to a signal line, and a second-conductivity-type layer located under the gate electrode, wherein the first-conductivity-type MOS output transistor transmits the output signal of the semiconductor apparatus to the output electrode responsive to a signal on the signal line;

a first-conductivity-type MOS protection transistor respectively including a drain electrode connected to the output electrode, a source electrode connected to the ground voltage terminal, and a gate electrode connected to the ground voltage terminal; and

a metallic wiring member which connects the second-conductivity-type layer of the first-conductivity-type MOS output transistor to the gate electrode of the first-conductivity-type MOS protection transistor;

wherein said first-conductivity-type MOS output transistor further includes a second-conductivity-type + area which is formed in said second-conductivity-type layer and substantially surrounds said drain electrode and said source electrode.